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(71) Applicant: **HITACHI LTD**

(72) Inventor: **OGINO MASAYOSHI  
TSUKAGOSHI MASAKI**

**(54) OUTSIDE DEFECT CHECKING METHOD**

(57) Abstract:

PURPOSE: To check defects in an outer appearance of a single reticle in a short time, by preliminarily forming a sacrifice pattern on a mask corresponding to a regular pattern and detecting outside defects of said mask through the identity of these patterns.

CONSTITUTION: Regular patterns 5W8 are formed in a single reticle (photomask) 1 and at the same time, sacrifice patterns 5'W8' are also formed. For detecting outside defects, only the patterns 1AW1C of the patterns formed on the reticle 1 are transferred onto a dummy wafer 9 by an exposing device. Then, the identity between the sacrifice patterns 5'W8' and regular patterns 5W8 on the dummy wafer 9 are compared by an outside defect checking device of a two-chip comparison type, and a non-identical part is detected as a defective one. Accordingly, even a single reticle or the like having single patterns formed thereon, its defects can be examined through the two-chip comparison.

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